EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	17663	(SiC or ((Si or silicon) adj carbide) or SiC?sub$3) near5 (substrate or wafer or support)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/04 13:07
L6	1127	3 near20 (opening or trench or groove or hole or via or recess$6 or viahole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/04 13:09
L13	948	6 and (@ad<"20030930" or @rlad<"20030930")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/04 14:16
L14	211	13 and ((opening or trench or groove or hole or via or recess$6 or viahole or aperture) near15 (heat or heatsink or heating or carbon or nanotube or nano))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/04 14:17

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L15	4014	(heatsink or (thermal or heated or heating) near5 (conductor or sink or relie$6)) same (carbon or nanotube or graphite or diamond)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/04 15:38
L19	668	15 and (SiC or ((Si or silicon) adj carbide) or SiC?sub$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/04 15:46
L21	520	19 and (@ad<"20030930" or @rlad<"20030930")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/04 15:47
L22	314	21 and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/04 15:47